

CORRECTED VERSION

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
31 March 2005 (31.03.2005)

PCT

(10) International Publication Number
WO 2005/029184 A3

(51) International Patent Classification⁷: G03F 7/023

(21) International Application Number:
PCT/JP2004/012235

(22) International Filing Date: 19 August 2004 (19.08.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-325953 18 September 2003 (18.09.2003) JP

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,

AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, GR, HU, ID, IL, IN, IS, KE, KG,
KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG,
MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH,
PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN,
TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW

(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE,
SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,
GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

(88) Date of publication of the international search report:
2 June 2005

(48) Date of publication of this corrected version:
9 March 2006

(15) Information about Correction:
see PCT Gazette No. 10/2006 of 9 March 2006, Section II

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: POSITIVE PHOTORESIST COMPOSITION AND RESIST PATTERN FORMATION

(57) Abstract: A means for increasing development velocity of a positive photoresist composition is provided which contains a photosensitive novolak resin formed by replacing some hydrogen atoms within those of all phenolic hydroxyl groups of alkali soluble novolak resin by 1,2-naphthoquinonediazide sulfonyl group. This means is positive photoresist composition and a formation method of a resist pattern using the composition which contains (A) a photosensitive novolak resin formed by replacing some hydrogen atoms within those of all phenolic hydroxyl groups of alkali soluble novolak resin by 1,2-naphthoquinonediazide sulfonyl group, which is dissolved in (B) propylene glycol alkyl ether acetate.

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